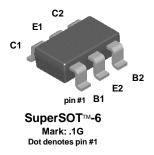


# FMBA06



# **NPN Multi-Chip General Purpose Amplifier**

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 33.

#### Absolute Maximum Ratings\* T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	80	V
V <sub>CBO</sub>	Collector-Base Voltage	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### **Thermal Characteristics** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FMBA06	
P <sub>D</sub>	Total Device Dissipation	700	mW
	Derate above 25°C	5.6	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	180	°C/W

These ratings are based on a maximum junction temperature of 150 degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# **NPN Multi-Chip General Purpose Amplifier**

Min

Тур

Max

(continued)

**Units** 

# **Electrical Characteristics**

**Parameter** 

T<sub>A</sub> = 25°C unless otherwise noted

**Test Conditions** 

OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Sustaining Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	80		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	4.0		V
I <sub>CEO</sub>	Collector-Cutoff Current	$V_{CE} = 60 \text{ V}, I_{B} = 0$		0.1	μΑ
I <sub>CBO</sub>	Collector-Cutoff Current	$V_{CB} = 80 \text{ V}, I_{E} = 0$		0.1	μΑ

#### **ON CHARACTERISTICS**

**Symbol** 

h <sub>FE</sub>	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100 100		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.25	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 1.0 V		1.2	V

#### SMALL SIGNAL CHARACTERISTICS

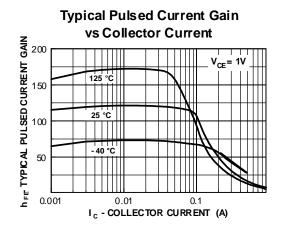
f⊤	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 2.0 \text{ V},$	100	MHz
		f = 100 MHz		

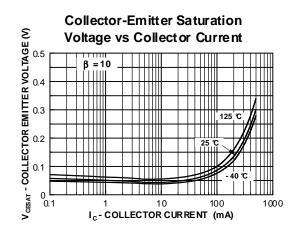
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

### **Spice Model**

NPN (Is=8.324f Xti=3 Eg=1.11 Vaf=100 Bf=12.16K Ne=1.368 Ise=73.27f Ikf=.1096 Xtb=1.5 Br=11.1 Nc=2 Isc=0 Ikr=0 Rc=.25 Cjc=18.36p Mjc=.3843 Vjc=.75 Fc=.5 Cje=55.61p Mje=.3834 Vje=.75 Tr=72.15n Tf=516.1p Itf=.5 Vtf=4 Xtf=6 Rb=10)

### **Typical Characteristics**

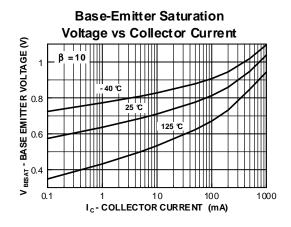


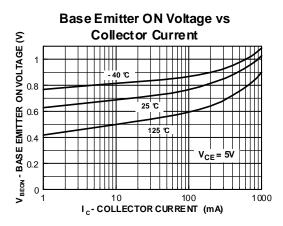


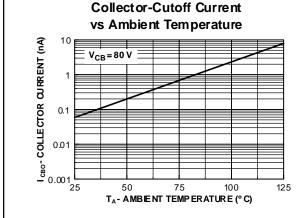
### NPN Multi-Chip General Purpose Amplifier

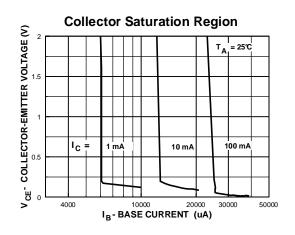
(continued)

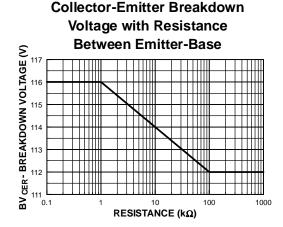
## Typical Characteristics (continued)

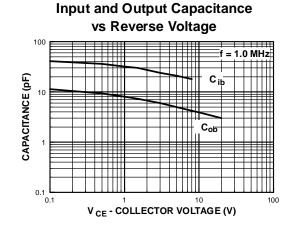








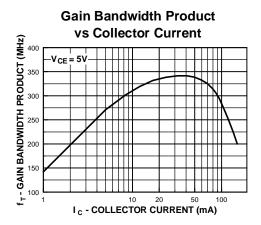


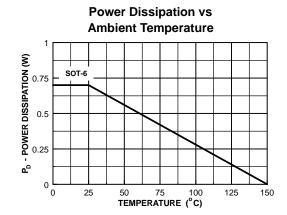


# **NPN Multi-Chip General Purpose Amplifier**

(continued)

# Typical Characteristics (continued)





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DOME™ Quiet Series™ ISOPLANAR™ E<sup>2</sup>CMOS<sup>TM</sup> MICROWIRE™ SILENT SWITCHER® EnSigna™ **OPTOLOGIC™** SMART START™ FACT™ **OPTOPLANAR™** SuperSOT™-3 FACT Quiet Series™ PACMAN™ SuperSOT™-6 **РОР**ТМ SuperSOT™-8 FAST®

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